

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a p-type well region, n⁺-type diffusion regions formed in the surface region of the p-type well region, a gate electrode containing silicon and formed above the p-type well region with a gate insulating film disposed therebetween, and NiSi films formed in the surface regions of the n⁺-type diffusion regions. In the semiconductor device, p-type impurity is doped in the depth direction from the surface of the NiSi film and the impurity profile of p-type impurity is so formed that a peak concentration of not lower than 1E20 cm⁻³ will be provided in a preset depth position of the NiSi film and the concentration in the interface between the NiSi film and the n⁺-type diffusion region and the concentration in a position deeper than the interface will not be higher than 5E19 cm⁻³.